

**HIGH ISOLATION VOLTAGE
4-PIN SOP PHOTOCOUPLER**

-NEPOC™ Series-

DESCRIPTION

The PS2761-1 is an optically coupled isolator containing a GaAs light emitting diode and an NPN silicon phototransistor.

This package is mounted in a plastic SOP (Small Outline Package) for high density applications.

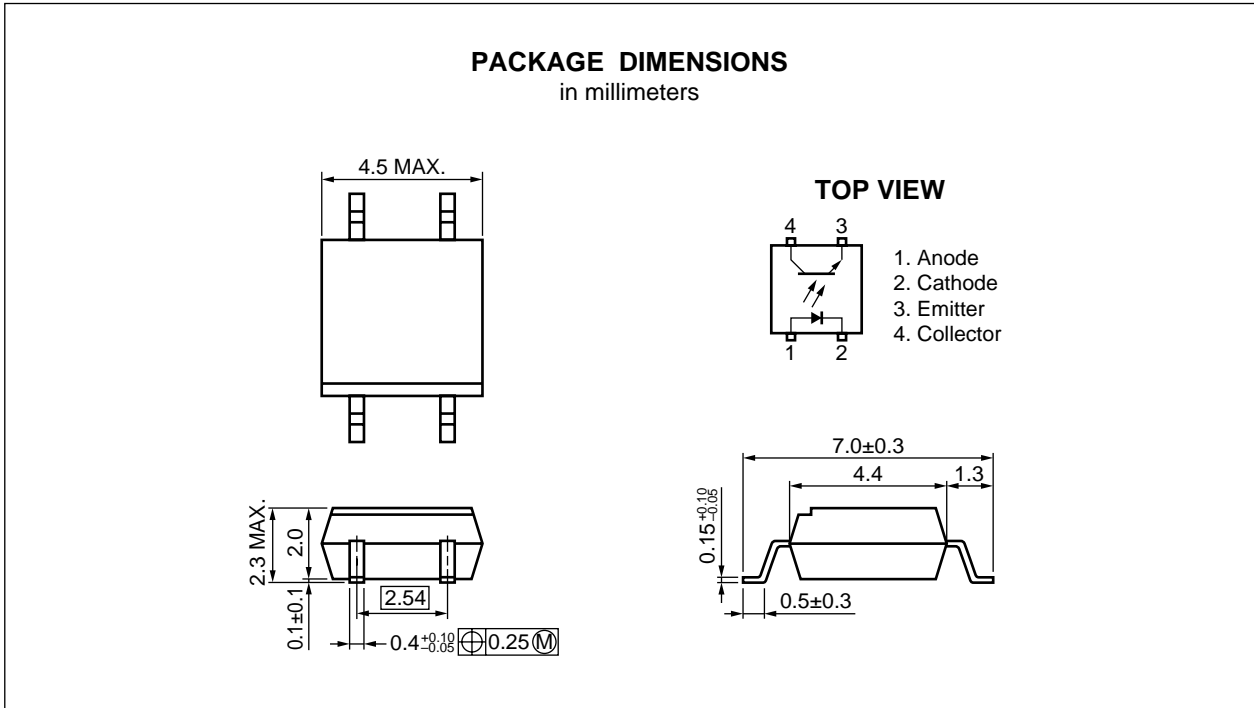
FEATURES

- High isolation thickness (0.4 mm MIN.)
- High isolation voltage (BV = 3 750 Vr.m.s.)
- SOP (Small Outline Package) type
- High-speed switching ($t_r = 3 \mu s$ TYP., $t_f = 5 \mu s$ TYP.)
- Ordering number of taping product: PS2761-1-E3, E4, F3, F4

APPLICATIONS

- Hybrid IC
- Programmable logic controllers
- Power supply

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Not all devices/types available in every country. Please check with local NEC representative for availability and additional information.



PHOTOCOUPLER CONSTRUCTION

Parameter	Unit (MIN.)
Air Distance	5 mm
Outer Distance	5 mm
Inner Distance	2.5 mm
Isolation Thickness	0.4 mm

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise specified)

Parameter		Symbol	Ratings	Unit
Diode	Forward Current (DC)	I _F	50	mA
	Reverse Voltage	V _R	6	V
	Power Dissipation Derating	ΔP _D /°C	0.8	mW/°C
	Power Dissipation	P _D	80	mW
	Peak Forward Current ¹	I _{FP}	1.0	A
Transistor	Collector to Emitter Voltage	V _{CEO}	40	V
	Emitter to Collector Voltage	V _{ECO}	6	V
	Collector Current	I _C	80	mA
	Power Dissipation Derating	ΔP _C /°C	1.5	mW/°C
	Power Dissipation	P _C	150	mW
Isolation Voltage ²		BV	3 750	Vr.m.s.
Operating Ambient Temperature		T _A	-40 to +100	°C
Storage Temperature		T _{stg}	-55 to +150	°C

*1 PW = 100 μs, Duty Cycle = 1 %

*2 AC voltage for 1 minute at T_A = 25 °C, RH = 60 % between input and output

ELECTRICAL CHARACTERISTICS (T_A = 25 °C)

Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Diode	Forward Voltage	V _F	I _F = 5 mA		1.1	1.4	V
	Reverse Current	I _R	V _R = 5 V			5	μA
	Terminal Capacitance	C _t	V = 0 V, f = 1 MHz		30		pF
Transistor	Collector to Emitter Dark Current	I _{CEO}	I _F = 0 mA, V _{CE} = 40 V			100	nA
Coupled	Current Transfer Ratio (I _C /I _F) ^{*1}	CTR	I _F = 5 mA, V _{CE} = 5 V	50	100	300	%
	Collector Saturation Voltage	V _{CE(sat)}	I _F = 10 mA, I _C = 2 mA			0.3	V
	Isolation Resistance	R _{I-O}	V _{I-O} = 1 kV _{DC}	10 ¹¹			Ω
	Isolation Capacitance	C _{I-O}	V = 0 V, f = 1 MHz		0.4		pF
	Rise Time	t _r	V _{CC} = 5 V, I _C = 2 mA, R _L = 100 Ω		3		μs
	Fall Time	t _f			5		

*1 CTR rank

M: 50 to 150 (%)

L: 100 to 300 (%)

CAUTION

Within this device there exists GaAs (Gallium Arsenide) material which is a harmful substance if ingested. Please do not under any circumstances break the hermetic seal.

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